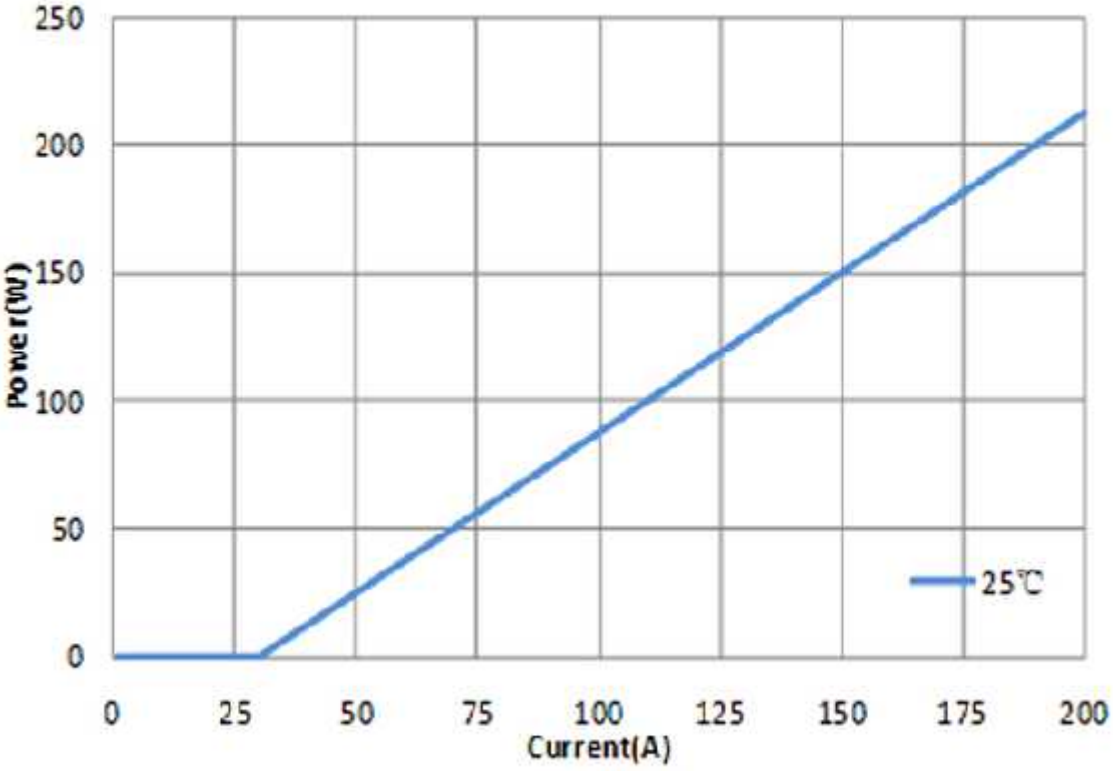
150W 808nm Laser Diode Chips
Bare Chips not bonded on Submount

Application:

Semiconductors for high-power diode lasers in direct material processing, for heating or lighting.
Semiconductors as pumping sources for fiber and solid-state lasers.
Use in printing technology. Esthetics, dermatology and surgery.

Data Sheet
Item No: LC808SB150
Item Name: 150W 808nm QCW Laser Diode Bars and Chips

Operation	
Center Wavelength	808nm
Output Power	150W
Operation Mode	QCW
Power modulation	100%
Geometrical	
Numbers of Emitters	60
Emitter width	120um
Cavity length	1000um
Emitter Pitch	160um
Filling factor	75%
Bar width	10000um
Thickness	125um
Electro Optical Data	
Threshold current	25A
Operating current	150-160A
Operating voltage	1.9-2.1V
Pulse wavelength	803nm
Conversion efficiency	50%
Slope efficiency	1.2W/A
Slow axis divergence	10
Fast axis divergence	39
Spectral width	4nm
Temperature characteristics	0.28nm/℃
Polarization	TE
LD operating temperature	25℃


250
200
150
100
50
0
Power(W)
0
25
50
75
100
125
150
175
200
Current(A)
25℃